Guowang Li

List of Publications by Year
in descending order

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31	1,419	18	24
papers	citations	h-index	g-index
		430874	610901

32	32	32	1297
all docs	docs citations	times ranked	citing authors

#	ARTICLE	IF	CITATIONS
1	Strained GaN quantum-well FETs on single crystal bulk AlN substrates. Applied Physics Letters, 2017, 110, .	3.3	48
2	High-voltage polarization-induced vertical heterostructure p-n junction diodes on bulk GaN substrates. , 2015, , .		3
3	Dual optical marker Raman characterization of strained GaN-channels on AlN using AlN/GaN/AlN quantum wells and 15N isotopes. Applied Physics Letters, 2015, 106, .	3.3	13
4	Two-dimensional electron gases in strained quantum wells for AlN/GaN/AlN double heterostructure field-effect transistors on AlN. Applied Physics Letters, 2014, 104, .	3.3	42
5	Polarization-Induced GaN-on-Insulator E/D Mode p-Channel Heterostructure FETs. IEEE Electron Device Letters, 2013, 34, 852-854.	3.9	55
6	Time delay analysis in high speed gate-recessed E-mode InAlN HEMTs. Solid-State Electronics, 2013, 80, 67-71.	1.4	7
7	Ultrascaled InAlN/GaN High Electron Mobility Transistors with Cutoff Frequency of 400 GHz. Japanese Journal of Applied Physics, 2013, 52, 08JN14.	1.5	66
8	InGaN Channel High-Electron-Mobility Transistors with InAlGaN Barrier and<i>f</i>_T/<i>f</i>_{max}of 260/220 GHz. Applied Physics Express, 2013, 6, 016503.	2.4	35
9	Quaternary Barrier InAlGaN HEMTs With f_{T}/f_{max} of 230/300 GHz. IEEE Electron Device Letters, 2013, 34, 378-380.	3.9	58
10	Ultra-thin Body GaN-on-insulator nFETs and pFETs: Towards III-nitride complementary logic. , 2012, , .		7
11	InAlN/AlN/GaN HEMTs With Regrown Ohmic Contacts and f_{T} of 370 GHz. IEEE Electron Device Letters, 2012, 33, 988-990.	3.9	292
12	Ultra-low resistance ohmic contacts to GaN with high Si doping concentrations grown by molecular beam epitaxy. Applied Physics Letters, 2012, 101, .	3.3	42
13	MBE-Regrown Ohmics in InAlN HEMTs With a Regrowth Interface Resistance of 0.05 $Omegacdothbox{mm}$. IEEE Electron Device Letters, 2012, 33, 525-527.	3.9	118
14	Ultrathin Body GaN-on-Insulator Quantum Well FETs With Regrown Ohmic Contacts. IEEE Electron Device Letters, 2012, 33, 661-663.	3.9	40
15	Effect of optical phonon scattering on the performance limits of ultrafast GaN transistors. , 2011, , .		2
16	Presence and origin of interface charges at atomic-layer deposited Al2O3/III-nitride heterojunctions. Applied Physics Letters, 2011, 99, .	3.3	140
17	Barrier height, interface charge & tunneling effective mass in ALD Al<inf>2</inf>O<inf>3</inf>/AlN/GaN HEMTs. , 2011, , .		3
18	Comparative study of E- and D-mode InAlN/AlN/GaN HEMTs with f<inf>T</inf> near 200 GHz. , 2011, , .		1

#	Article	IF	Citations
19	210-GHz InAlN/GaN HEMTs With Dielectric-Free Passivation. IEEE Electron Device Letters, 2011, 32, 892-894.	3.9	88
20	220-GHz Quaternary Barrier InAlGaN/AlN/GaN HEMTs. IEEE Electron Device Letters, 2011, 32, 1215-1217.	3.9	71
21	Si-Containing Recessed Ohmic Contacts and 210 GHz Quaternary Barrier InAlGaN High-Electron-Mobility Transistors. Applied Physics Express, 2011, 4, 096502.	2.4	10
22	MBE growth of high conductivity single and multiple AlN/GaN heterojunctions. Journal of Crystal Growth, 2011, 323, 529-533.	1.5	45
23	Metalâ€face InAlN/AlN/GaN high electron mobility transistors with regrown ohmic contacts by molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1617-1619.	1.8	25
24	Subcritical barrier AlN/GaN E/Dâ€mode HFETs and inverters. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1620-1622.	1.8	16
25	Polarizationâ€engineering in group IIIâ€nitride heterostructures: New opportunities for device design. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1511-1516.	1.8	83
26	High mobility two-dimensional electron gases in nitride heterostructures with high Al composition AlGaN alloy barriers. Applied Physics Letters, 2010, 97, .	3.3	14
27	Threshold Voltage Control in $hbox{Al}_{0.72} hbox{Ga}_{0.28}hbox{N/AlN/GaN}$ HEMTs by Work-Function Engineering. IEEE Electron Device Letters, 2010, 31, 954-956.	3.9	47
28	Quantum transport in graphene nanoribbons patterned by metal masks. Applied Physics Letters, 2010, 96, .	3.3	45
29	High performance E-mode InAlN/GaN HEMTs: Interface states from subthreshold slopes. , 2010, , .		1
30	Work-function engineering in novel high Al composition Al<inf>0.72</inf>Ga<inf>0.28</inf>N/AlN/GaN HEMTs. , 2010, , .		0
31	Quantum transport in patterned graphene nanoribbons. , 2009, , .		1